Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) A transistor device structure formed on a substrate, the substrate defining a substantially horizontal plane, the semiconductor transistor device structure comprising:
 - a source region;
 - a drain region;
- a gate electrode disposed on the substrate, said gate electrode positioned vertically between said source region and said drain region; and
- a plurality of semiconducting nanotubes, each of said semiconducting nanotubes including a first end electrically coupled with said source region, a second end electrically coupled with said drain region, and a channel region extending vertically through said gate electrode between said source region and said drain region, and said gate electrode configured to receive a control voltage effective to regulate current flow through said channel region between said source region and said drain region.
- 2. (Currently Amended) The transistor device structure of claim 1 wherein said source <u>region</u> is composed of a catalyst material effective for growing said semiconducting nanotubes.
- 3. (Currently Amended) The transistor device structure of claim 1 wherein said drain <u>region</u> is composed of a catalyst material effective for growing said semiconducting nanotubes.

- 4. (Currently Amended) The transistor device structure of claim 1 further comprising: an insulating layer disposed between said drain <u>region</u> and said gate electrode.
- 5. (Currently Amended) The transistor device structure of claim 1 further comprising: an insulating layer disposed between said source <u>region</u> and said gate.
- 6. (Previously Presented) The transistor device structure of claim 1 wherein said semiconducting nanotubes are composed of arranged carbon atoms.
- 7. (Cancelled)
- 8. (Previously Presented) The transistor device structure of claim 1 wherein said semiconducting nanotubes are oriented substantially perpendicular to said horizontal plane.
- 9-34. (Cancelled)